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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

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ON Semiconductor®

FDS4141

P-Channel PowerTrench® MOSFET

-40V, -10.8A, 13.0mΩ

Features

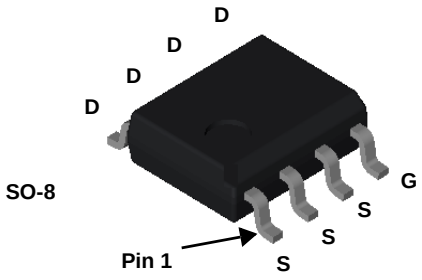
- Max $r_{DS(on)}$ = 13.0mΩ at V_{GS} = -10V, I_D = -10.5A
- Max $r_{DS(on)}$ = 19.0mΩ at V_{GS} = -4.5V, I_D = -8.4A
- High performance trench technology for extremely low $r_{DS(on)}$
- RoHS Compliant

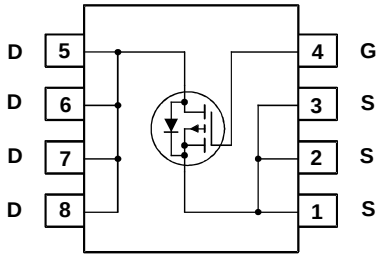
General Description

This P-Channel MOSFET has been produced using On Semiconductor's proprietary PowerTrench® technology to deliver low $r_{DS(on)}$ and optimized BV_{DSS} capability to offer superior performance benefit in the applications and optimized switching performance capability reducing power dissipation losses in converter/inverter applications.

Applications

- Control switch in synchronous & non-synchronous buck
- Load switch
- Inverter





MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			-40	V
V_{GS}	Gate to Source Voltage			±20	V
I_D	Drain Current -Continuous			-10.8	A
	-Pulsed			-36	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	294	mJ
P_D	Power Dissipation	T_A = 25°C	(Note 1a)	5	W
	Power Dissipation	T_A = 25°C	(Note 1b)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	25	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS4141	FDS4141	SO-8	13''	12mm	2500units

Semiconductor Components Industries, LLC, 2017
April, 2017, Rev. 1.0

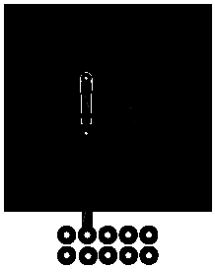
Publication Order Number:
FDS4141

Electrical Characteristics T_J = 25°C unless otherwise noted

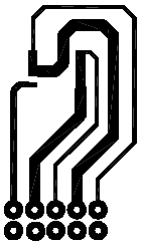
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = -250μA, V_{GS} = 0V	-40			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = -250μA, referenced to 25°C		-33		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -32V,			-1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = -250μA	-1.0	-1.6	-3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = -250μA, referenced to 25°C		5.3		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = -10V, I_D = -10.5A		11.0	13.0	mΩ
		V_{GS} = -4.5V, I_D = -8.4A		15.2	19.0	
		V_{GS} = -10V, I_D = -10.5A, T_J= 125°C		16.8	19.9	
g_{FS}	Forward Transconductance	V_{DD} = -5V, I_D = -10.5A		37		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -20V, V_{GS} = 0V, f = 1MHz		2005	2670	pF
C_{oss}	Output Capacitance			355	475	pF
C_{rss}	Reverse Transfer Capacitance			190	285	pF
R_g	Gate Resistance	f = 1MHz		5		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = -20V, I_D = -10.5A, V_{GS} = -10V, R_{GEN} = 6Ω		10	20	ns
t_r	Rise Time			5	10	ns
$t_{d(off)}$	Turn-Off Delay Time			42	68	ns
t_f	Fall Time			12	22	ns
Q_g	Total Gate Charge	V_{GS} = 0V to -10V; V_{DD} = -20V, I_D = -10.5A		35	49	nC
Q_g	Total Gate Charge	V_{GS} = 0V to -5V; V_{DD} = -20V, I_D = -10.5A		19	27	nC
Q_{gs}	Gate to Source Charge	V_{DD} = -20V, I_D = -10.5A		6		nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = -20V, I_D = -10.5A		7		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = -10.5A (Note 2)		-0.8	-1.3	V
		V_{GS} = 0V, I_S = -2.1A (Note 2)		-0.7	-1.2	
t_{rr}	Reverse Recovery Time	I_F = -10.5A, di/dt = 100A/μs		26	42	ns
Q_{rr}	Reverse Recovery Charge			14	26	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50°C/W when mounted on a 1in^2 pad of 2 oz copper.



b) 125°C/W when mounted on a minimum pad.

2. Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.

3. UIL condition: Starting T_J = 25°C, L = 3mH, I_{AS} = -14A, V_{DD} = -40V, V_{GS} = -10V.

Typical Characteristics T_J = 25°C unless otherwise noted

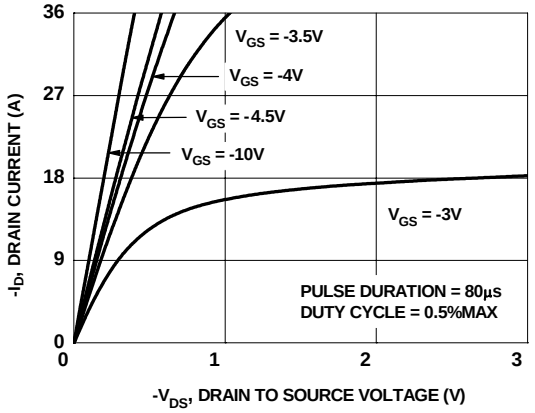


Figure 1. On-Region Characteristics

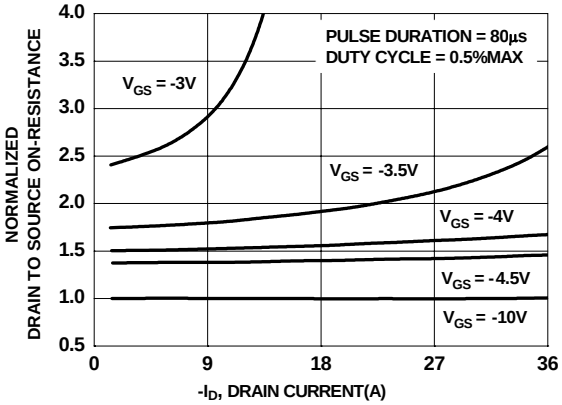


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

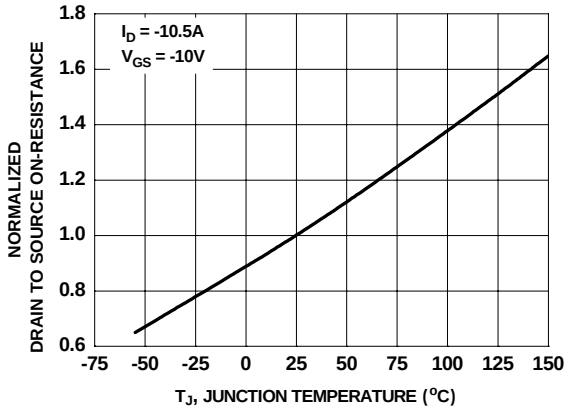


Figure 3. Normalized On-Resistance vs Junction Temperature

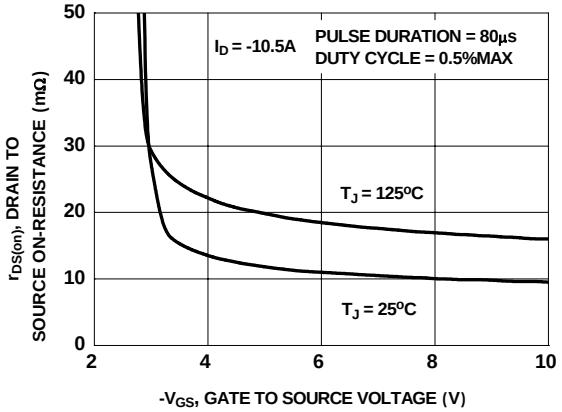


Figure 4. On-Resistance vs Gate to Source Voltage

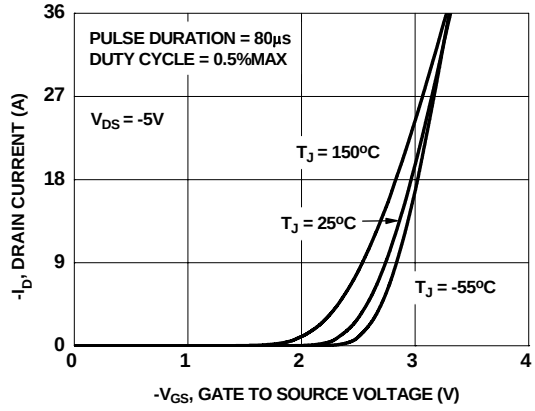


Figure 5. Transfer Characteristics

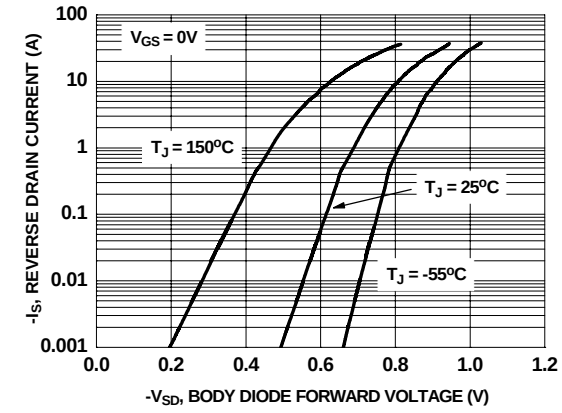


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

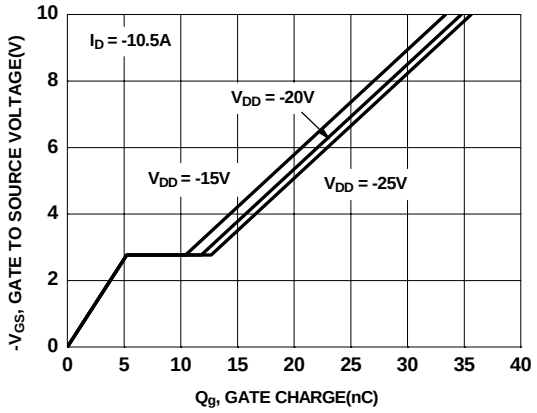


Figure 7. Gate Charge Characteristics

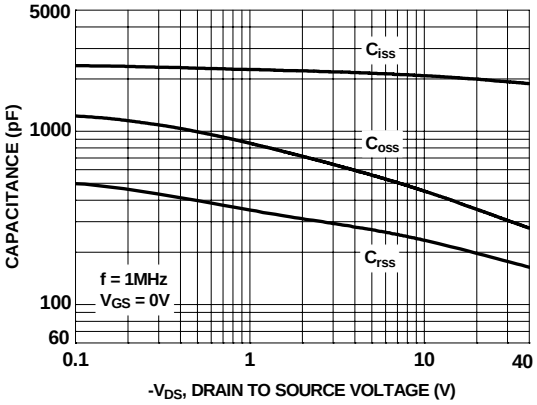


Figure 8. Capacitance vs Drain to Source Voltage

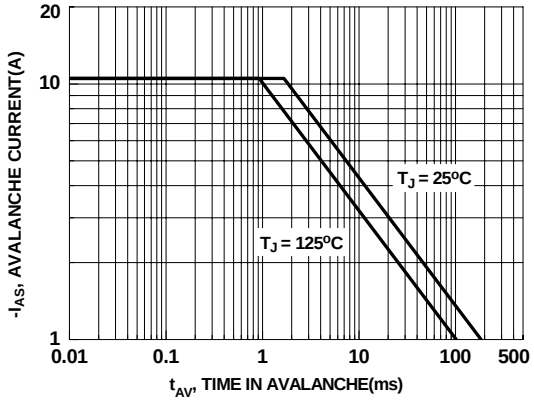


Figure 9. Unclamped Inductive Switching Capability

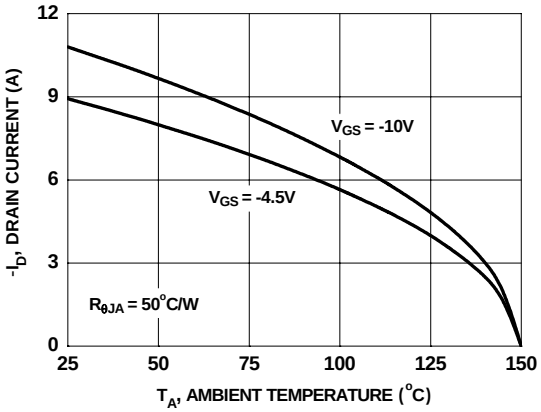


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

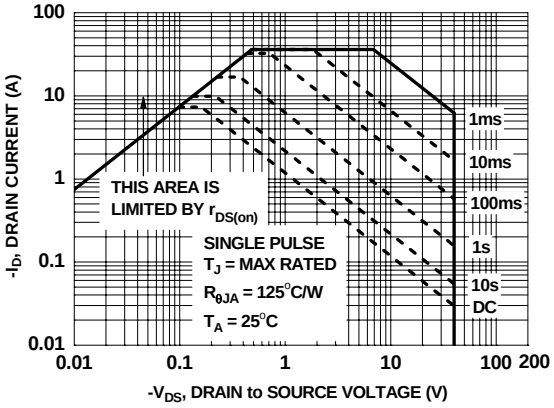


Figure 11. Forward Bias Safe Operating Area

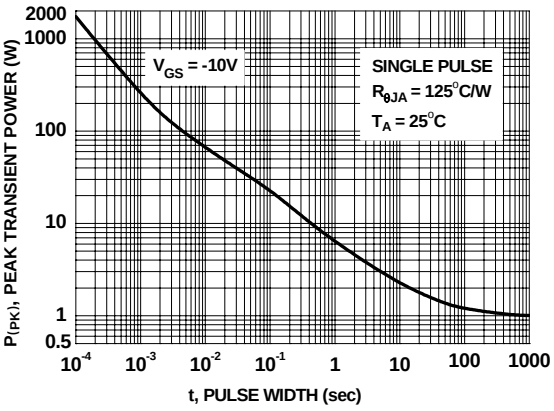


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted

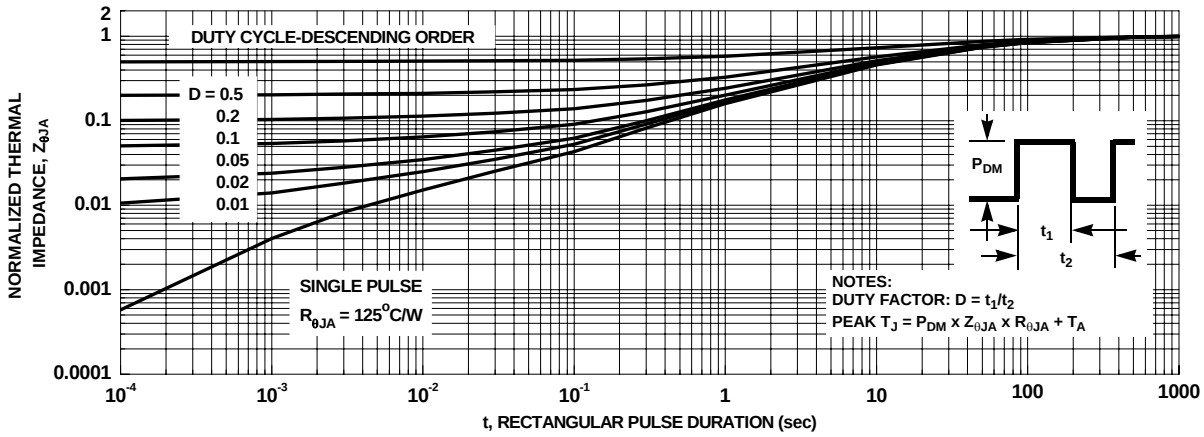
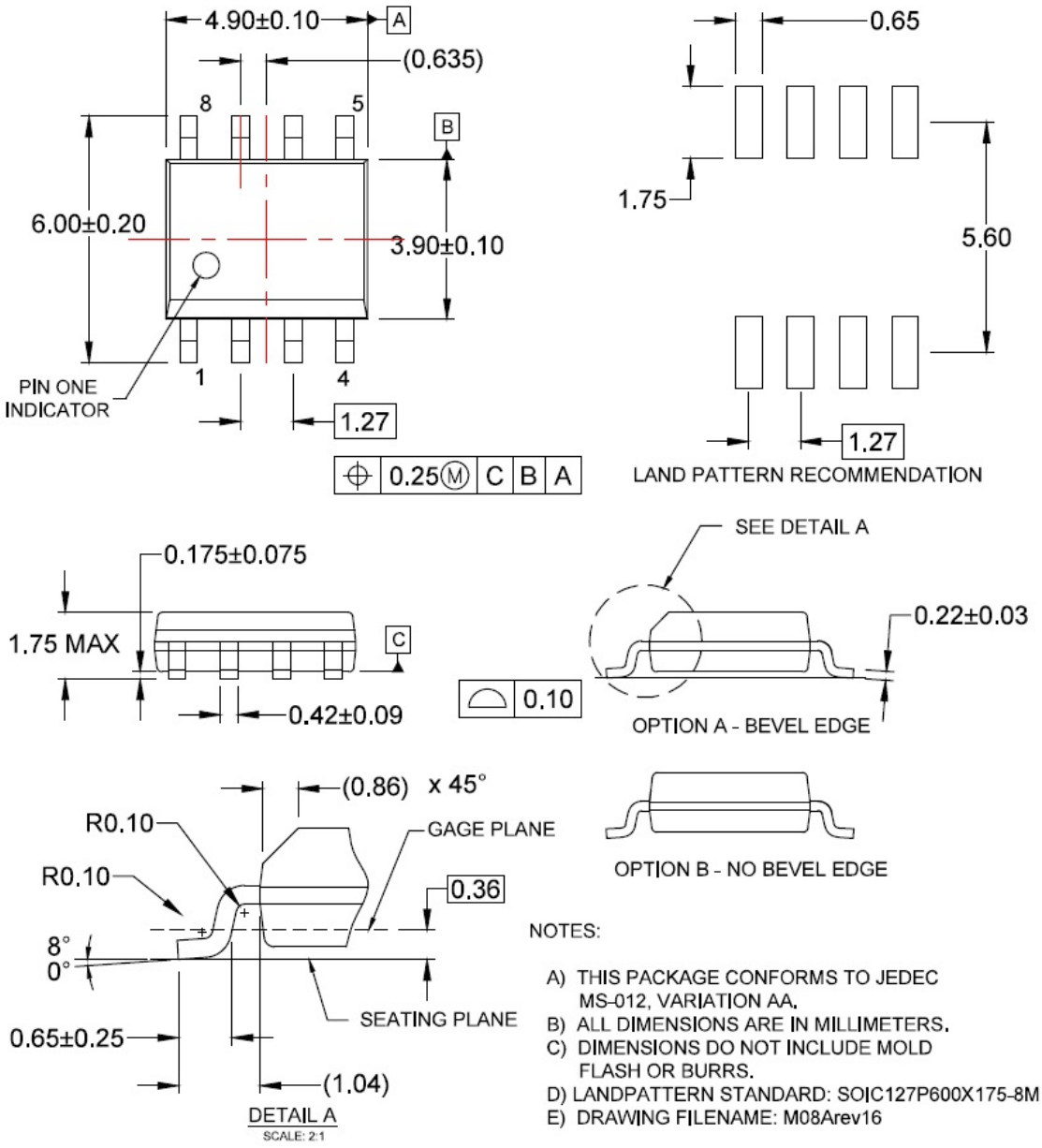


Figure 13. Transient Thermal Response Curve

Dimensional Outline and Pad Layout



NOTES:

A) THIS PACKAGE CONFORMS TO JEDEC MS-012, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
D) LANDPATTERN STANDARD: SOIC127P600X175-8M
E) DRAWING FILENAME: M08Arev16

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